

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Docket Number (Optional) YOR919990509US3 (13171AB)	Application Number Unassigned 10/827064
	Applicant(s) Cyril Cabral, Jr., et al.	
	Filing Date Herewith 4/19/04	Group Art Unit Unassigned 2813

U.S. PATENT DOCUMENTS

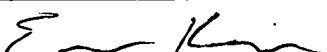
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EL		5,510,295	4/23/96	Cabral, Jr., et al.	—	—	
		5,608,226	3/4/97	Yamada, et al.	—	—	
		5,624,869	4/29/97	Agnello, et al.	—	—	
		5,828,131	10/27/98	Cabral, Jr., et al.	—	—	
		5,830,775	11/1998	Maa, et al.	—	—	
		5,710,450	1/1998	Chau, et al.	—	—	
		6,121,100	9/2000	Andideh, et al.	—	—	
		6,165,826	12/2000	Chau, et al.	—	—	
		6,211,560 B1	4/2001	Jimenez, et al.	—	—	
		6,326,664 B1	12/2001	Chau, et al.	—	—	

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REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EL	M. Lawrence, et al., "Growth of Epitaxial CoSi ₂ on (100) Si, "Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310 (1991).
EL	Wolf, Silicon Processing for the VLSI Era, Vol. 2-Process Intergration, Lattice Press: Sunset Beach CA, 1990, pp. 144-151.
EL	C. Cabral, et al., "In-Situ X-Ray Diffractin and Resistivity Analysis of CoSi ₂ Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates, "Mat. Res. Soc. Symp. Proc., Vol. 375, pp. 253-258 (1995).

EXAMINER 	DATE CONSIDERED 12/11/2004
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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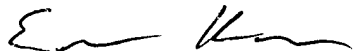
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK		4,965,645 A	10/1990	Solomon.	—	—	
EK		5,336,903 A	8/1994	Ozturk, et al.	—	—	
EK		5,401,674 A	3/1995	Anjum, et al.	—	—	

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							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EK	Huang, et al. "Impact of Ge implantation on the electrical characteristics of TiSi2 p+n shallow junctions with an a-Si (or poly-Si) buffer layer" in IEEE Transactions on Electron Devices, 44(4), April 1997, pp. 601-606.
EK	Prabhakaran, et al. "Diffusion mediated chemical reaction in Co/Ge/Si(100) forming Ge/CoSi2/Si(100)" in Applied Physics Letters 68(9), 26 February 1996, pp. 1241-1243.

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